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(54) Title: MEMRISTOR ARRAY AND METHOD OF MANUFACTURING THEREOF

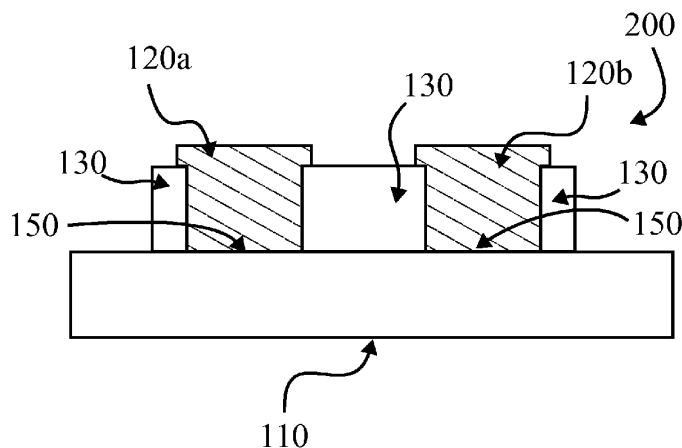


FIG. 2B

(57) Abstract: A memristor array (200), comprising a plurality of memristor devices, the memristor devices comprising: a first pattern (110) comprising memristive material with formula $Gd_{1-x}Ca_xMnO_3$, wherein x has a value more than 0.6 and less than 0.99; a second pattern (120a, 120b) comprising oxidizable metal, wherein the second pattern (120a, 120b) is in contact with the first pattern over an interface (150) comprising at least one oxide of the oxidizable metal; wherein at least one memristor device of the memristor array (200) is connected to at least one other memristor device of the memristor array (200) via at least the first pattern (110).

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